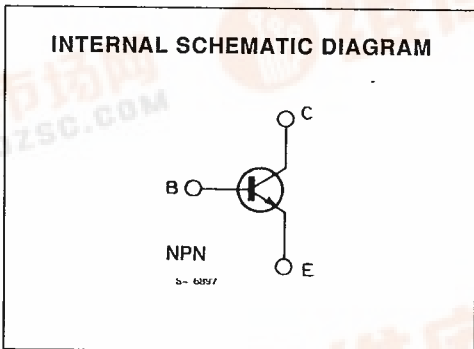
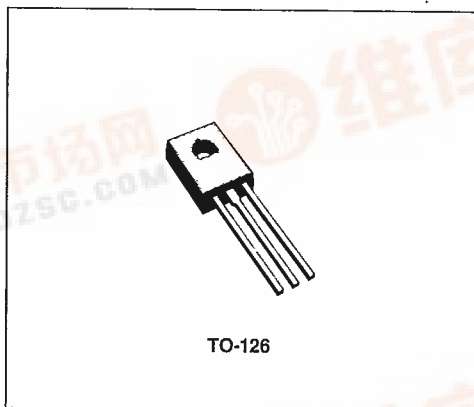


DESCRIPTION

The BU325 is a silicon planar epitaxial NPN transistor in Jedec TO-126 plastic case. It is intended for high voltage, high current linear and switching applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	200	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	200	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	5	V
I_C	Collector Current	3	A
I_B	Base Current	1	A
P_{tot}	Total Power Dissipation at $T_{amb} \leq 25\text{ }^\circ\text{C}$ $T_{case} \leq 25\text{ }^\circ\text{C}$	1.25 25	W W
T_{stg}	Storage Temperature	- 65 to 150	$^\circ\text{C}$
T_j	Junction Temperature	150	$^\circ\text{C}$



THERMAL DATA

SGS-THOMSON

30E D

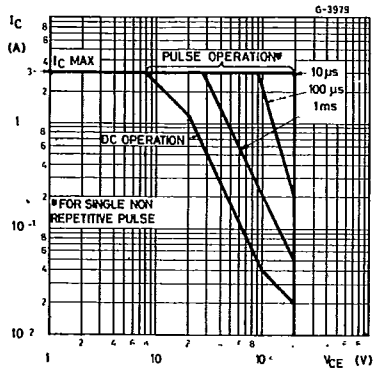
$R_{thj-case}$	Thermal Resistance Junction-case	Max	5	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-amb.	Max	100	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cutoff Current ($I_E = 0$)	$V_{CB} = 200 V$			100	μA
V_{CBO}	Collector-base Breakdown Voltage ($I_E = 0$)	$I_C = 100 \mu A$	200			V
$V_{CEO(sus)}^*$	Collector-emitter Sustaining Voltage ($I_B = 0$)	$I_C = 10 mA$	200			V
V_{EBO}^*	Emitter-base Voltage ($I_C = 0$)	$I_E = 1 mA$	5			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 150 mA$ $I_C = 500 mA$	$I_B = 15 mA$ $I_B = 50 mA$	0.06 0.10	1.0 1.5	V V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = 150 mA$ $I_C = 500 mA$	$I_B = 15 mA$ $I_B = 50 mA$	0.73 0.80	1.0 1.2	V V
h_{FE}^*	DC Current Gain	$I_C = 50 mA$ $I_C = 150 mA$ $I_C = 500 mA$	$V_{CE} = 5 V$ $V_{CE} = 5 V$ $V_{CE} = 5 V$	30 30 30	200 200 200	
f_T	Transition Frequency	$I_C = 500 mA$	$V_{CE} = 5 V$	40		MHz
C_{CBO}	Collector-base Capacitance	$I_E = 0$ $f = 1 MHz$	$V_{CB} = 10 V$		50	pF
t_{on}	Turn-on Time	$I_C = 0.5 A$ $V_{CC} = 20 V$	$I_{B1} = 50 mA$	0.3		μs
t_{off}	Turn-off Time	$I_C = 0.5 A$ $I_{B1} = -I_{B2} = 50 mA$ $V_{CC} = 20 V$		1		μs

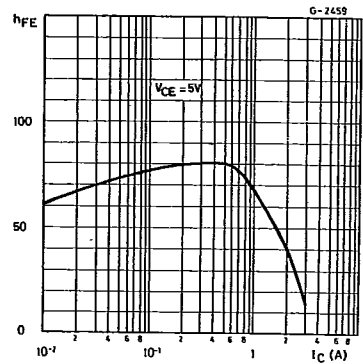
* Pulsed : pulse duration = 300 μs , duty cycle = 1.5 %.

Safe Operating Area.



DC Current Gain.

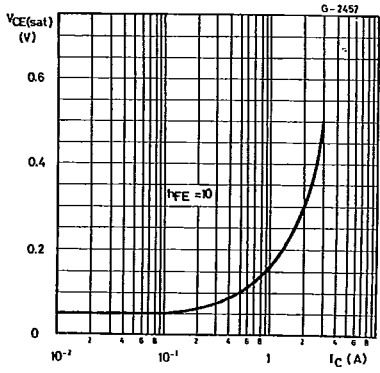
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Collector-emitter Saturation Voltage.

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30E D

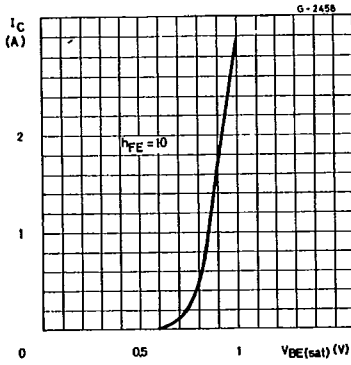


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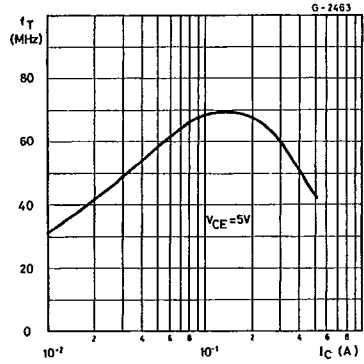
30E D

Base-emitter Saturation Voltage.

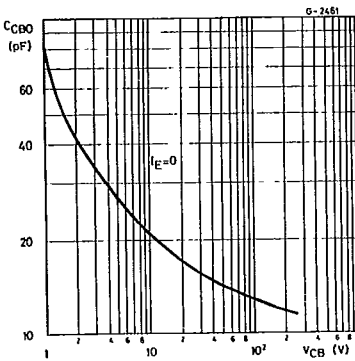
Transition Frequency.



Collector-emitter Saturation Voltage.



Saturated Switching Characteristics.



Power Rating Chart.

